## **Claims**

Claims 1-19 (cancelled)

20. (currently amended) The method of claim 18 A method comprising:

providing a chalcogenide vapor comprising As and chalcogen in a molar ratio of X,

wherein X is between about 1:19 and about 3:4; and

growing substantially amorphous chalcogenide nanowires on a preselected portion of a substrate exposed to the chalcogenide vapor wherein the chalcogenide nanowires have a molar ratio of As to chalcogen within about 10% of X, and wherein the chalcogenide nanowires are grown on a biocompatible surface of an implant.

21. (currently amended) The method of claim 18 A method comprising:

providing a chalcogenide vapor comprising As and chalcogen in a molar ratio of X,

wherein X is between about 1:19 and about 3:4; and

growing substantially amorphous chalcogenide nanowires on a preselected portion of a substrate exposed to the chalcogenide vapor wherein the chalcogenide nanowires have a molar ratio of As to chalcogen within about 10% of X, and wherein the chalcogenide nanowires are grown on an optical fiber.

22. (original) The method of claim 21 wherein the optical fiber is substantially transparent to infrared light.

Claims 23-40 (cancelled)

41. (currently amended) The method of claim 40 A method comprising:

providing microscale structures on an implant by subliming a material to provide a vapor

phase and depositing the vapor phase onto a surface of the implant such that microscale

structures of the vapor phase are formed on a preselected portion of the implant wherein the

structures comprise nanowires, and wherein the nanowires comprise chalcogenide.

- 42. (currently amended) The method of claim 39 A method comprising:

  providing microscale structures on an implant by subliming a material to provide a vapor

  phase and depositing the vapor phase onto a surface of the implant such that microscale

  structures of the vapor phase are formed on a preselected portion of the implant wherein the

  structures comprise chalcogenide.
  - 43. (original) The method of claim 42 wherein the chalcogenide comprises Se.

Claim 44 (cancelled)

45. (currently amended) The method of claim 44 A method comprising:

providing microscale structures on an implant by subliming a material to provide a vapor

phase and depositing the vapor phase onto a surface of the implant such that microscale

structures of the vapor phase are formed on a preselected portion of the implant wherein the

structures comprise micro-crystals and wherein the micro-crystals comprise As<sub>2</sub>O<sub>3</sub>.